



12N70

Power MOSFET

12A, 700V N-CHANNEL POWER MOSFET

DESCRIPTION

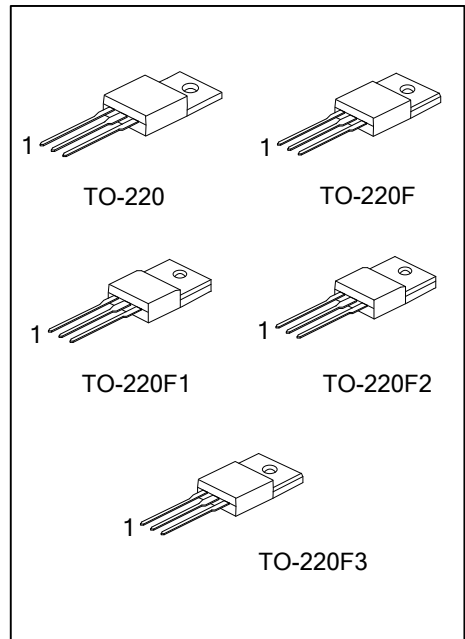
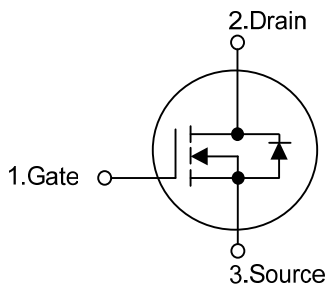
The UTC **12N70** are N-Channel enhancement mode power MOSFET which are produced using UTC's proprietary, planar stripe, DMOS technology.

These devices are suited for high efficiency switch mode power supply. To minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode the advanced technology has been especially tailored.

FEATURES

- * $R_{DS(ON)} < 1.0\Omega @ V_{GS} = 10V$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
12N70L-TA3-T	12N70G-TA3-T	TO-220	G	D	S	Tube
12N70L-TF3-T	12N70G-TF3-T	TO-220F	G	D	S	Tube
12N70L-TF1-T	12N70G-TF1-T	TO-220F1	G	D	S	Tube
12N70L-TF2-T	12N70G-TF2-T	TO-220F2	G	D	S	Tube
12N70L-TF3T-T	12N70G-TF3T-T	TO-220F3	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>12N70L-TA3-T</p> <p>(1) Packing Type (2) Package Type (3) Lead Free</p>	<p>(1) T: Tube (2) TA3: TO-220, TF3: TO-220F, TF1: TO220-F1, TF2: TO-220F2, TF3T: TO-220F3 (3) L: Lead Free, G: Halogen Free</p>
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MARKING INFORMATION

PACKAGE	MARKING
TO-220 TO-220F TO-220F1 TO-220F2 TO-220F3	<p>UTC 12N70 □ □ □ □ □ □ 1</p> <p>Lot Code ← → Data Code</p> <p>L: Lead Free G: Halogen Free</p>

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	12	A
Drain Current	Continuous	I_D	12	A
	Pulsed (Note 2)	I_{DM}	48	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	790	mJ
	Repetitive (Note 2)	E_{AR}	24	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220	P_D	225	$^\circ\text{C/W}$
	TO-220F/TO-220F1		52	$^\circ\text{C/W}$
	TO-220F3		55	$^\circ\text{C/W}$
	TO-220F2			
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

- Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 2. Repetitive Rating: Pulse width limited by maximum junction temperature
 3. $L=10\text{mH}$, $I_{AS}=12\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$
 4. $I_{SD} \leq 12\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C/W}$
Junction to Case	TO-220	θ_{JC}	0.56	$^\circ\text{C/W}$
	TO-220F/TO-220F1		2.40	$^\circ\text{C/W}$
	TO-220F3			
	TO-220F2		2.27	$^\circ\text{C/W}$

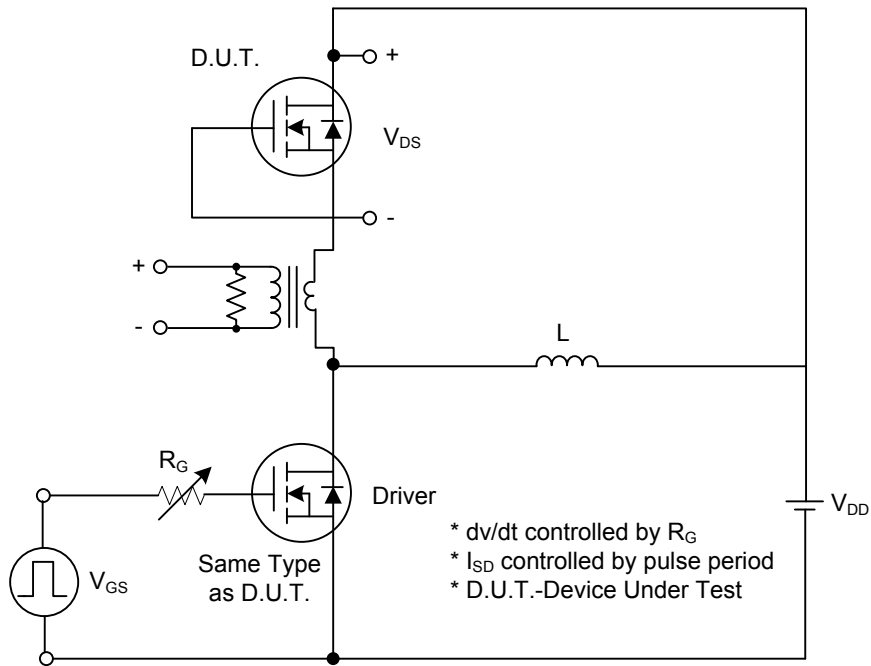
■ ELECTRICAL CHARACTERISTICS (T_C = 25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 250 μA	700			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 700 V, V _{GS} = 0 V			10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = ±30 V, V _{DS} = 0 V			±100	nA
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D = 250 μA, Referenced to 25°C		0.7		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250 μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 6.0A		0.7	1.0	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1MHz		1600	1900	pF
Output Capacitance	C _{OSS}			160	270	pF
Reverse Transfer Capacitance	C _{RSS}			25	35	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 30V, I _D = 0.5A, R _G = 25Ω (Note 1, 2)		96	120	ns
Turn-On Rise Time	t _R			158	240	ns
Turn-Off Delay Time	t _{D(OFF)}			370	400	ns
Turn-Off Fall Time	t _F			180	220	ns
Total Gate Charge	Q _G	V _{DS} = 50V, I _D = 1.3A, V _{GS} = 10 V (Note 1, 2)		56	60	nC
Gate-Source Charge	Q _{GS}			10		nC
Gate-Drain Charge	Q _{GD}			17		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 12A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I _S				12	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				48	A
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, I _S = 12A, dI _F /dt = 100 A/μs (Note 1)		380		ns
Reverse Recovery Charge	Q _{RR}			3.5		μC

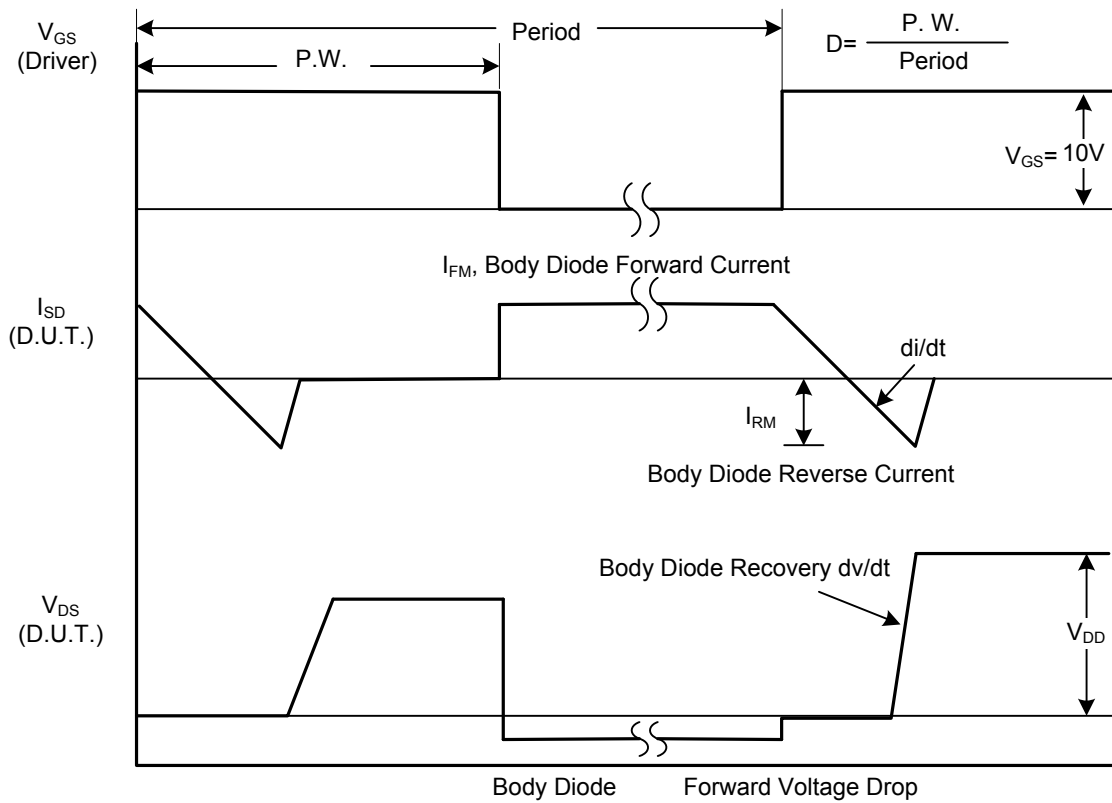
Notes: 1. Pulse Test: Pulse width ≤ 300 μs, Duty cycle ≤ 2%

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

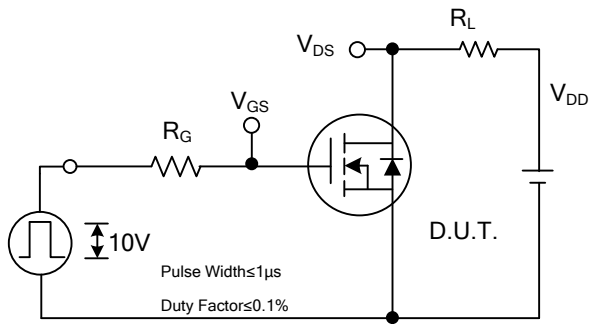


Peak Diode Recovery dv/dt Test Circuit

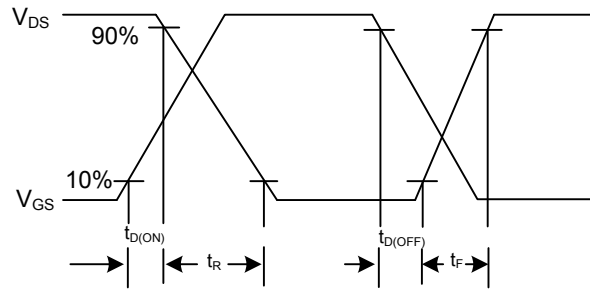


Peak Diode Recovery dv/dt Waveforms

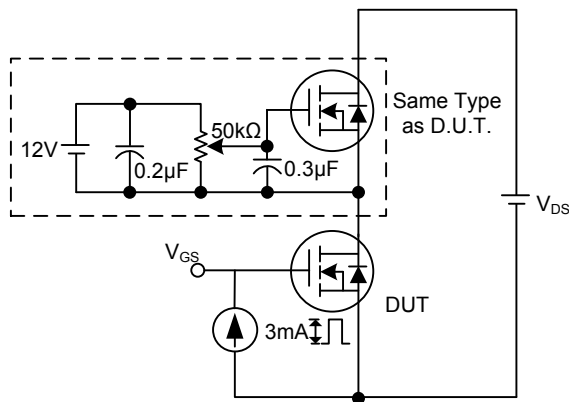
TEST CIRCUITS AND WAVEFORMS (Cont.)



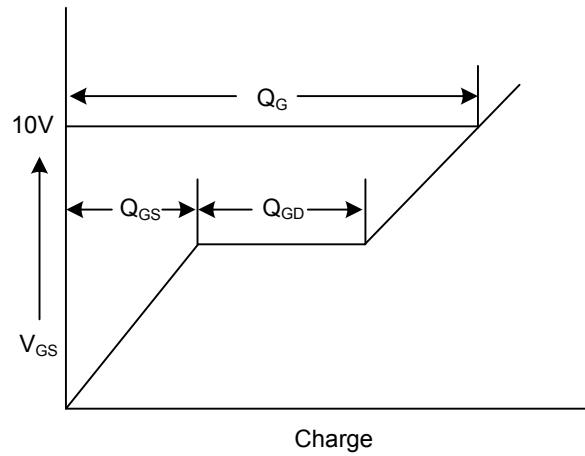
Switching Test Circuit



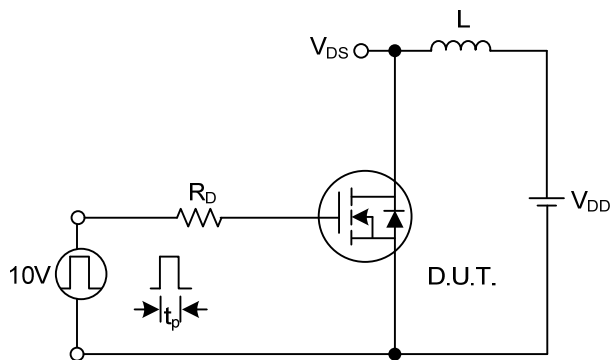
Switching Waveforms



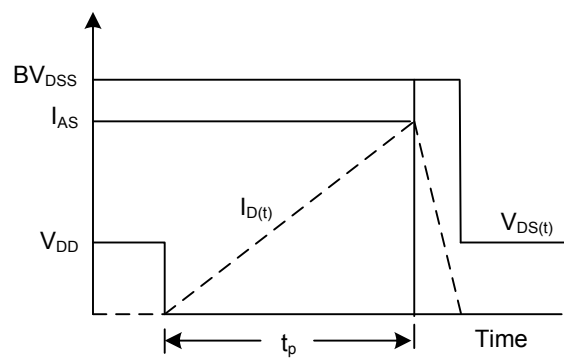
Gate Charge Test Circuit



Gate Charge Waveform

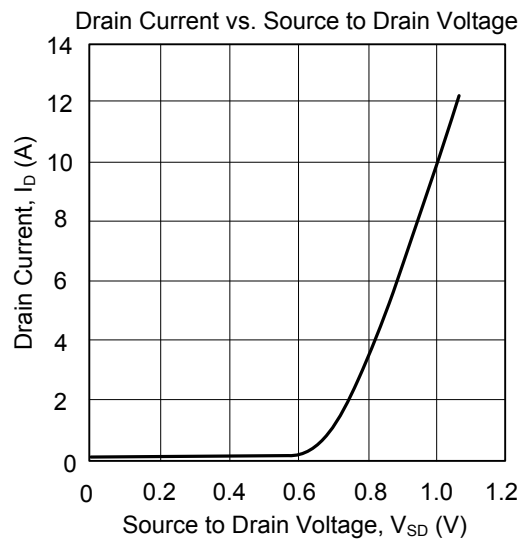
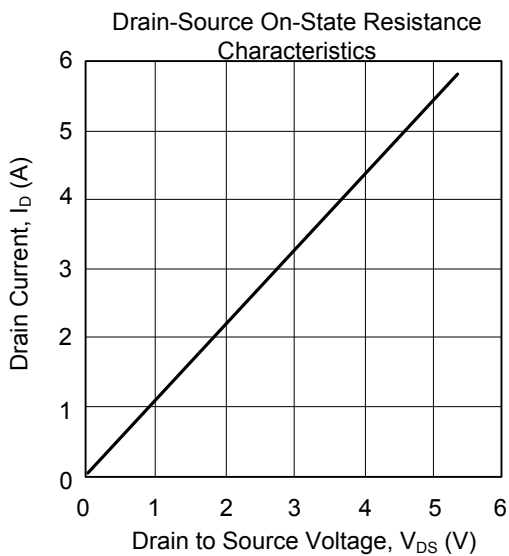
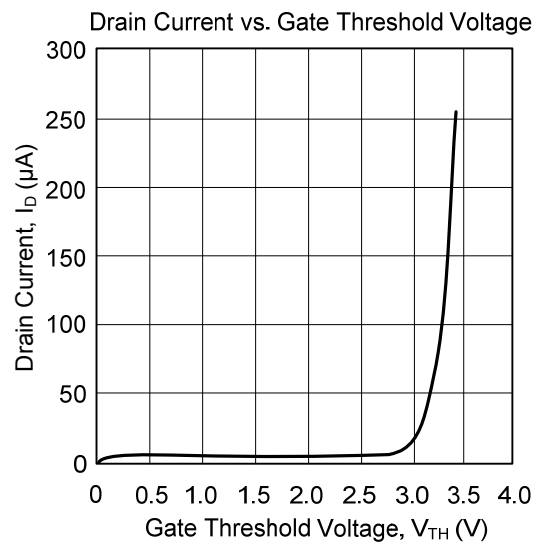
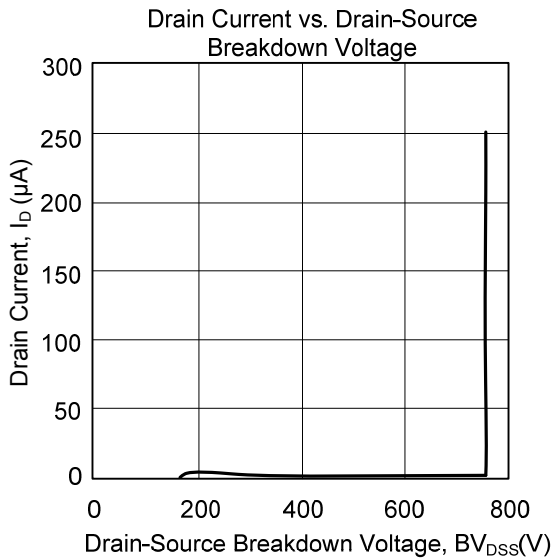


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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